

### **In the Specification**

Please amend the title as follows:

~~Methods of Forming Implant Regions Relative to Transistor Gates~~ Semiconductor  
Constructions.

At page 1, before the "Technical Field" section, please insert:

### **RELATED PATENT DATA**

This patent resulted from a continuation application of U.S. Patent Application Serial  
No. 10/326,725, which was filed December 20, 2002, and which issued April 20, 2004 as  
U.S. Patent 6,723,623.